

In Situ Plasma Process To Remove Fluorine Residue:
From the Interior Surfaces of A CVD Reactor
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CHEMICAL VAPOR DEPOSITION (CVD) OR PLASMA ENHANCED CVD OF SILICON OR TUNGSTEN CONTAINING FILMS IN A CVD CHAMBER.

FLUORINE BASED CLEANING PLASMA (IN SITU OR REMOTE) TO REMOVE DEPOSITS FROM THE INTERIOR SURFACES OF THE CVD CHAMBER.

IN SITU CLEANING PLASMA OF A
HYDROGEN CONTAINING GAS AND AN
OXYGEN CONTAINING GAS TO REMOVE
FLUORINE RESIDES FROM THE INTERIOR
SURFACES OF THE CVD CHAMBER.

Figure 1



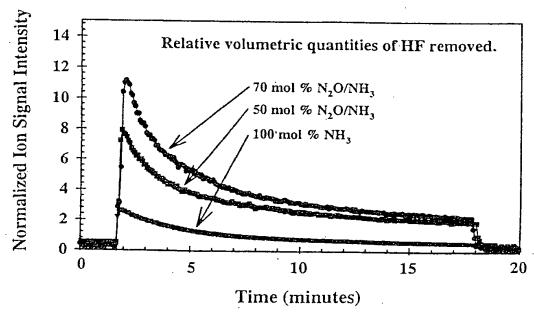


Figure 2

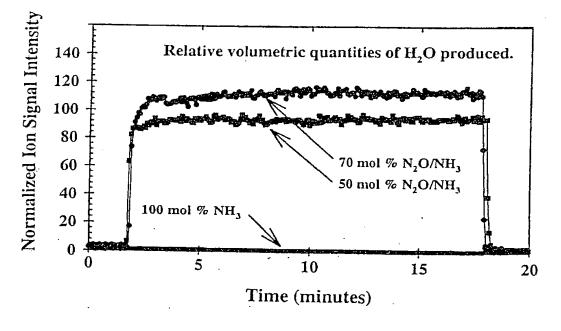


Figure 3

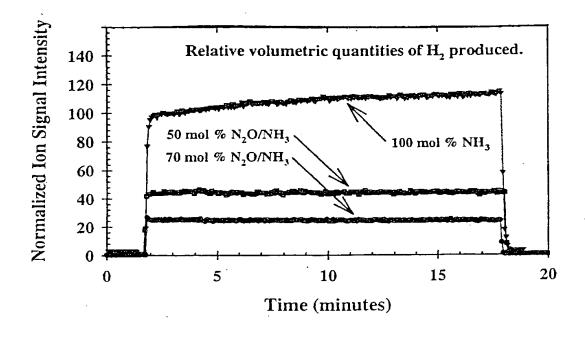
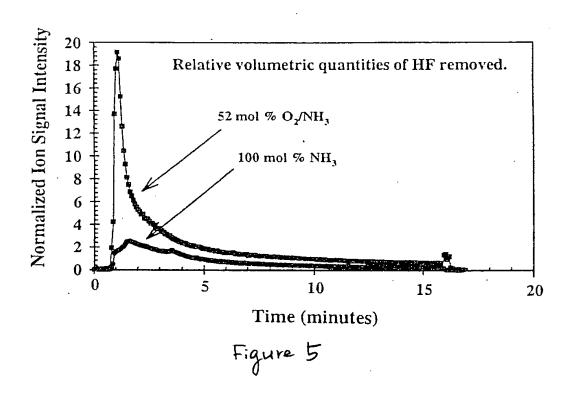
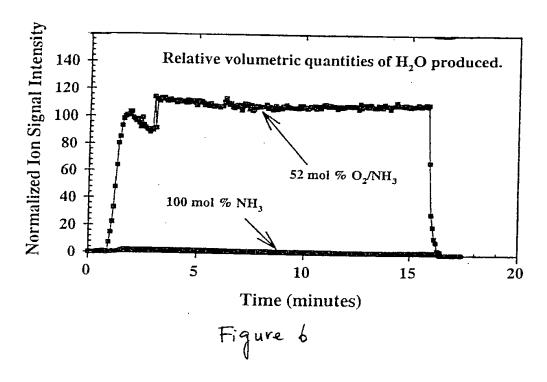


Figure 4





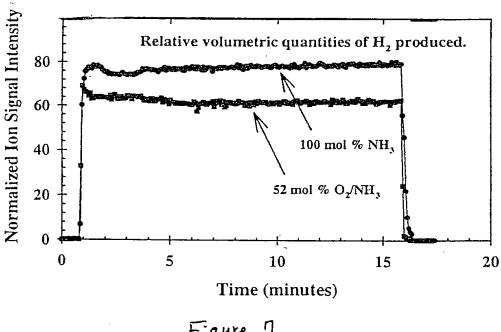


Figure 7